

SANYO	No.4207	2SK1895
		N-Channel MOS Silicon FET Very High-Speed Switching Applications

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating mounting.

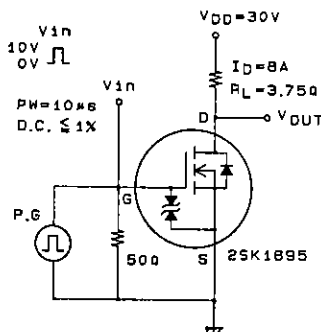
Absolute Maximum Ratings at Ta = 25°C

Drain to Source Voltage	V _{DSS}	60	V
Gate to Source Voltage	V _{GSS}	±15	V
Drain Current(DC)	I _D	12	A
Drain Current(Pulse)	I _{DP}	PW ≤ 10μs, duty cycle ≤ 1%	
Allowable Power Dissipation	P _D	2.0	W
		T _c = 25°C	
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150 °C	

Electrical Characteristics at Ta = 25°C

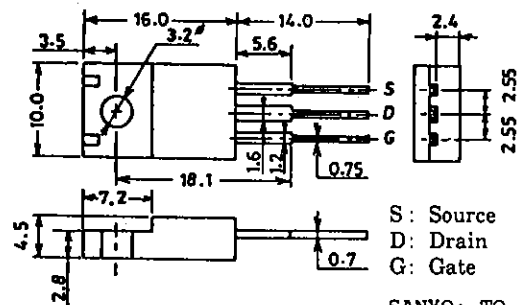
		min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS} I _D = 1mA, V _{GS} = 0	60			V
G-S Breakdown Voltage	V _{(BR)GSS} I _G = ±100μA, V _{DS} = 0	±15			V
Zero Gate Voltage Drain Current	I _{DSS} V _{DS} = 60V, V _{GS} = 0			100	μA
Gate to Source Leakage Current	I _{GSS} V _{GS} = ±12V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)} V _{DS} = 10V, I _D = 1mA	1.0		2.0	V
Forward Transfer Admittance	Y _{fs} V _{DS} = 10V, I _D = 8A	6.5	10.5		S
Static Drain to Source on State Resistance	R _{DS(on)} I _D = 8A, V _{GS} = 10V		60	80	mΩ
	R _{DS(on)} I _D = 8A, V _{GS} = 4V		80	110	mΩ
Input Capacitance	C _{iss} V _{DS} = 20V, f = 1MHz		950		pF
Output Capacitance	C _{oss} V _{DS} = 20V, f = 1MHz		250		pF
Reverse Transfer Capacitance	C _{rss} V _{DS} = 20V, f = 1MHz		50		pF
Turn-ON Delay Time	t _{d(on)} See specified Test Circuit.		13		ns
Rise Time	t _r "		40		ns
Turn-OFF Delay Time	t _{d(off)} "		95		ns
Fall Time	t _f "		80		ns
Diode Forward Voltage	V _{SD} I _S = 12A, V _{GS} = 0	1.0	1.5		V

Switching Time Test Circuit

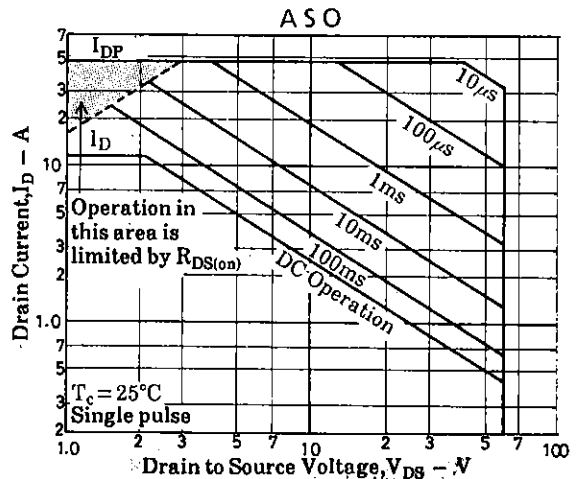
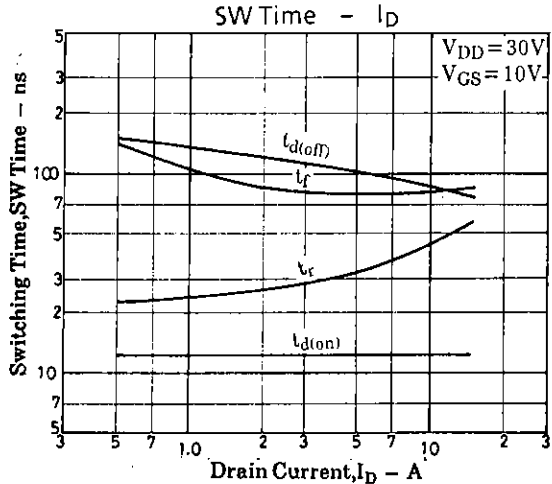
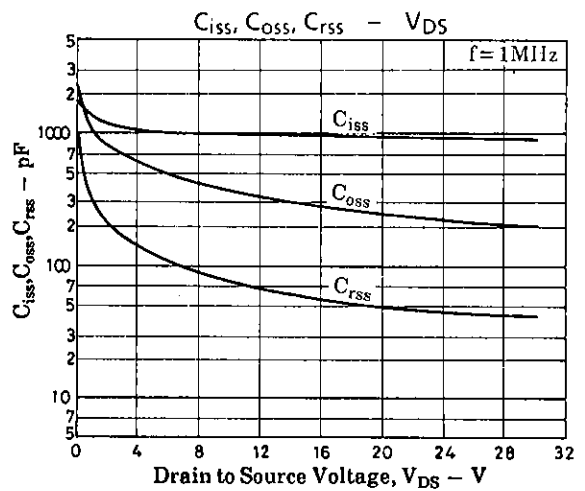
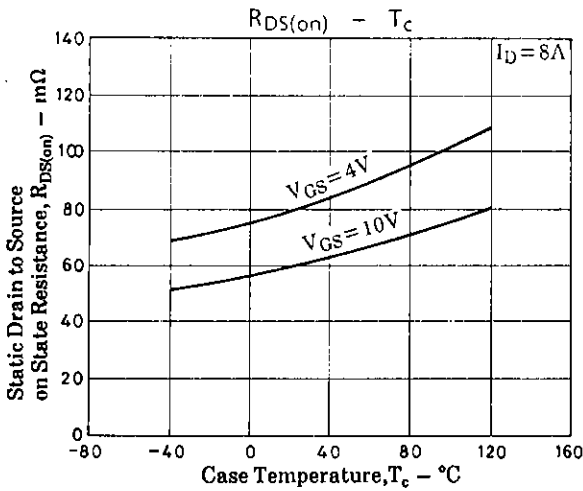
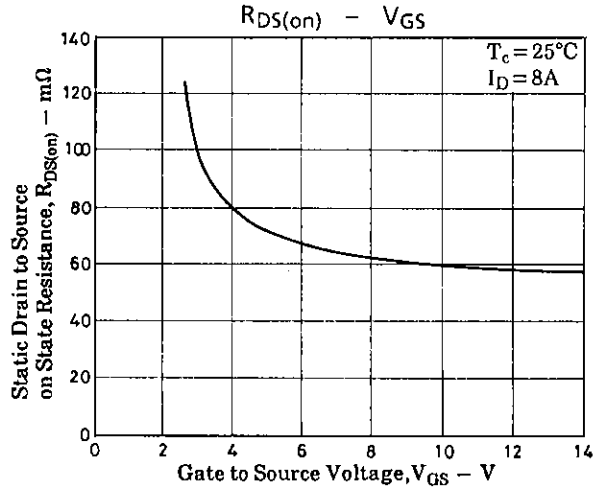
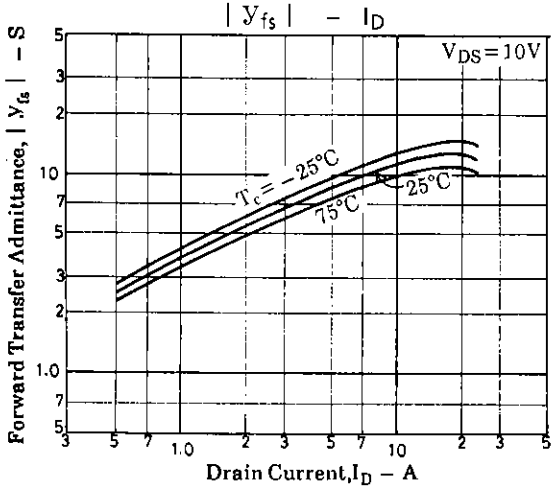
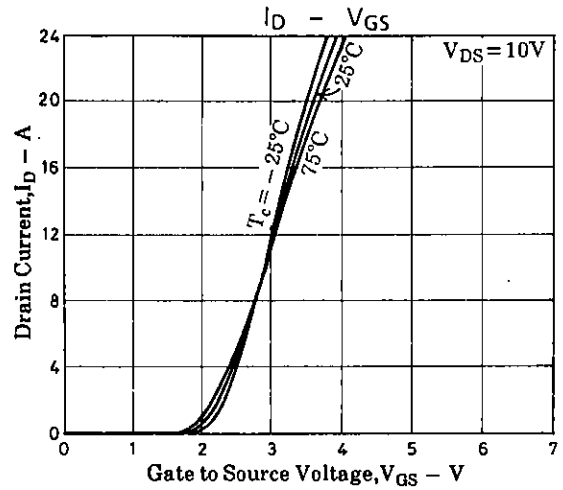
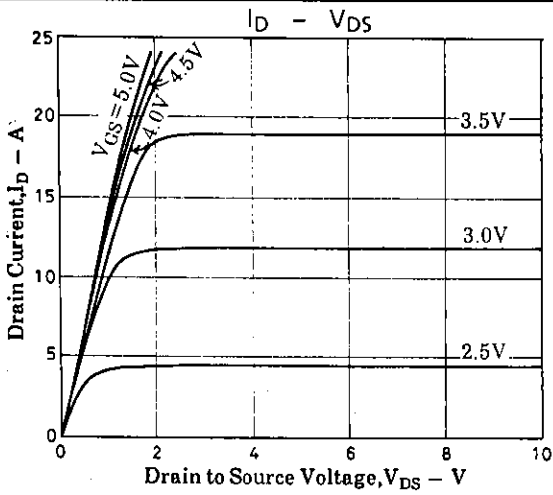


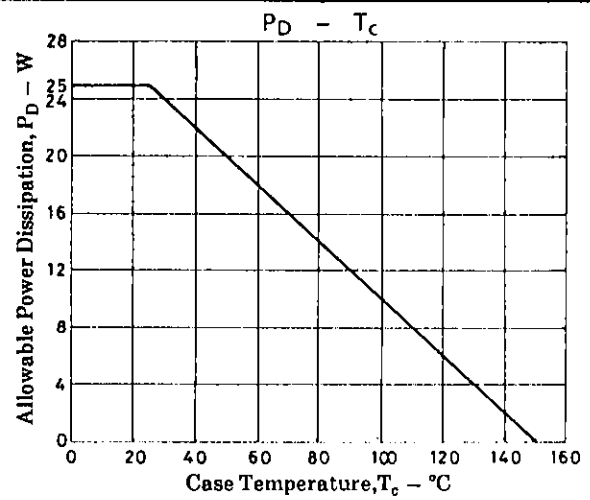
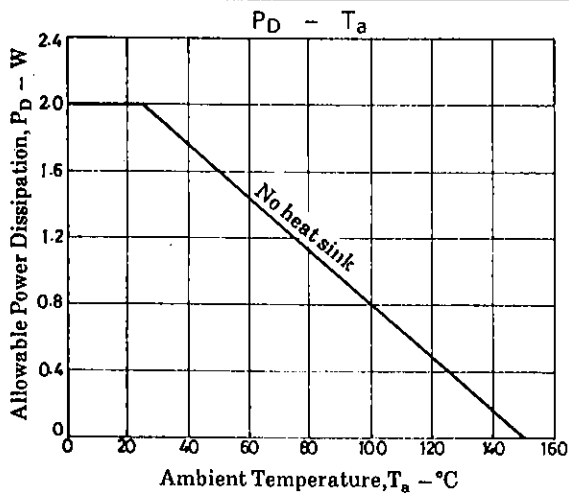
Package Dimensions 2063

(unit: mm)



SANYO: TO-220ML





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